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semiconductor film and function to promote the crystallization
of the semiconductor film;

forming a gettering layer over said semiconductor film
after the crystallization; and

heating said semiconductor film and said gettering
layer at a temperature from 500°C to 800°C in order to getter the
catalyst metal in said semiconductor film using said gettering
layer.

34. (Amended) A method of manufacturing a device
comprising the steps of:

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providing a substantially intrinsic semiconductor film
on an insulating surface;

providing said semiconductor film with a catalyst
metal-containing material;

crystallizing said semiconductor film by heating in a
way that causes said catalyst metal to diffuse through the
semiconductor film and function to promote the crystallization
of said semiconductor film;

forming a gettering layer over said semiconductor film
after the crystallization; and

heating said semiconductor film and said gettering
layer in order to getter the catalyst metal in said
semiconductor film by said gettering layer.

42. (Amended) A method of manufacturing a device
comprising the steps of.

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providing a semiconductor film on an insulating
surface;

providing a catalyst metal-containing material on said
semiconductor film;

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crystallizing said semiconductor film by heating in a way that causes said catalyst metal to diffuse through the semiconductor film and function to promote the crystallization of said semiconductor film;

forming a gettering layer over said semiconductor film after the crystallization; and

heating said semiconductor film and said gettering layer in a nitrogen atmosphere in order to getter the catalyst metal contained in said semiconductor film by said gettering layer.

51. (Amended) A method of manufacturing a device having a junction, said method comprising the steps of:

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providing a semiconductor film comprising amorphous silicon on an insulating surface;

providing a catalyst metal-containing material on said semiconductor film;

crystallizing said semiconductor film by heating in a way that causes said metal to diffuse through the semiconductor film and to promote the crystallization thereof;

forming a gettering layer over said semiconductor film after the crystallization;

heating said semiconductor film and said gettering layer at a temperature from 500°C to 800°C in order to getter the metal included in said semiconductor film by said gettering layer; and

forming a doped semiconductor film on said semiconductor film to form a junction.

59. (Amended) A method of manufacturing a device having a junction, said method comprising the steps of:

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providing a substantially intrinsic semiconductor film on an insulating surface;

providing a catalyst metal on said semiconductor film;
crystallizing said semiconductor film by heating to cause said catalyst metal to diffuse through the semiconductor film and to promote the crystallization of said semiconductor film;

forming a gettering layer over said semiconductor film after the crystallization thereof;

heating said semiconductor film and said gettering layer in order to getter the catalyst metal in said semiconductor film by said gettering layer; and

forming a junction using said intrinsic semiconductor film.

67. (Amended) A method of manufacturing a device having a junction, said method comprising the steps of:

providing a semiconductor film comprising amorphous silicon formed on an insulating surface;

providing a catalyst metal-containing material on said semiconductor film;

crystallizing said semiconductor film by heating in a way that causes said catalyst metal to diffuse through the semiconductor film and function to promote the crystallization of said semiconductor film;

forming a gettering layer over said semiconductor film after the crystallization; and

heating said semiconductor film and said gettering layer in a nitrogen atmosphere in order to getter the catalyst metal contained in said semiconductor film by said gettering layer; and

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forming a junction on said semiconductor film.

76. (Amended) A method of manufacturing a device,
comprising the steps of:

providing a semiconductor film on an insulating
surface;

forming a catalyst metal-containing material on said
semiconductor film, said catalyst being a material which
facilitates crystallization of said semiconductor film, but
which when present in a final product of the device degrades
operation of the device;

crystallizing said semiconductor film by heating in a
way that causes said catalyst metal-containing material to
diffuse into at least a part of the semiconductor film, said
catalyst metal-containing material when so diffused functioning
to facilitate said crystallization;

forming a gettering layer over said semiconductor film
after said crystallization; and

processing said semiconductor film and said gettering
layer to remove at least one portion of said catalyst metal in
said semiconductor film.

81. (Amended) A method of manufacturing a device
comprising the steps of:

providing a semiconductor film on an insulating
surface;

providing said semiconductor film with a metal-
containing material;

crystallizing said semiconductor film by heating in a
way that causes said metal to diffuse through the semiconductor

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film and function to promote the crystallization of the semiconductor film;

introducing a gettering element into a portion of said crystallized semiconductor film;

heating said semiconductor film after introducing said gettering element at a temperature from 500°C to 800°C in order to getter the metal in said semiconductor film; and

removing said portion after gettering the metal in said semiconductor film.

82. (Amended) A method of manufacturing a device comprising the steps of:

providing a semiconductor film doped with boron at a concentration of 0.001-0.1 atm% on an insulating surface;

providing said semiconductor film with a metal-containing material;

crystallizing said semiconductor film by heating in a way that causes said metal to diffuse through the semiconductor film and function to promote the crystallization of said semiconductor film;

forming a gettering layer over said semiconductor film after the crystallization; and

heating said semiconductor film and said gettering layer in order to getter the metal in said semiconductor film by said gettering layer.

83. (Amended) A method of manufacturing a device comprising the steps of:

providing a substantially intrinsic semiconductor film on an insulating surface;

providing said semiconductor film with a metal-containing material;

crystallizing said semiconductor film by heating in a way that causes said metal to diffuse through the semiconductor film and function to promote the crystallization of said semiconductor film;

introducing a gettering element into a portion of the crystallized semiconductor film;

heating said semiconductor film after introducing said gettering element in order to getter the metal in said semiconductor film; and

removing said portion after gettering the metal in said semiconductor film.

84. (Amended) A method of manufacturing a device comprising the steps of:

providing a semiconductor film doped with boron at a concentration of 0.001-0.1 atm% on an insulating surface;

providing said semiconductor film with a metal-containing material;

crystallizing said semiconductor film by heating in a way that causes said metal to diffuse through the semiconductor film and function to promote the crystallization of said semiconductor film;

introducing a gettering element into a portion of the crystallized semiconductor film;

heating said semiconductor film after introducing said gettering element in order to getter the metal in said semiconductor film; and

removing said portion after gettering the metal in said semiconductor film.

85. (Amended) A method of manufacturing a device comprising the steps of:

providing a semiconductor film on an insulating surface;

providing a metal-containing material on said semiconductor film;

crystallizing said semiconductor film by heating in a way that causes said metal to diffuse through the semiconductor film and function to promote the crystallization of said semiconductor film;

introducing a gettering element into a portion of the crystallized semiconductor film;

heating said semiconductor film in a nitrogen atmosphere after introducing said gettering element in order to getter the metal contained in said semiconductor film; and

removing said portion after gettering the metal in said semiconductor film.

86. (Amended) A method of manufacturing a device having a junction, said method comprising the steps of:

providing a semiconductor film doped with boron at a concentration of 0.001-0.1 atm% on an insulating surface;

providing a metal on said semiconductor film;

crystallizing said semiconductor film by heating to cause said metal to diffuse through the semiconductor film and to promote the crystallization of said semiconductor film;

forming a gettering layer over said semiconductor film after the crystallization thereof;

heating said semiconductor film and said gettering layer in order to getter the metal in said semiconductor film by said gettering layer; and
forming a junction using an intrinsic semiconductor film.

87. (Amended) A method of manufacturing a device having a junction, said method comprising the steps of:

providing a substantially intrinsic semiconductor film on an insulating surface;

providing a metal on said semiconductor film;

crystallizing said semiconductor film by heating to cause said metal to diffuse through the semiconductor film and to promote the crystallization of said semiconductor film;

introducing a gettering element into a portion of the crystallized semiconductor film ~~(by plasma doping);~~

heating said semiconductor film after introducing said gettering element in order to getter the metal in said semiconductor film by said phosphorus;

removing said portion after gettering the metal in said semiconductor film; and

forming a junction using a doped semiconductor film.

88. (Amended) A method of manufacturing a device having a junction, said method comprising the steps of:

providing a semiconductor film doped with boron at a concentration of 0.001-0.1 atm% on an insulating surface;

providing a metal on said semiconductor film;

crystallizing said semiconductor film by heating to cause said metal to diffuse through the semiconductor film and to promote the crystallization of said semiconductor film;

introducing a gettering element into a portion of the crystallized semiconductor film;

heating said semiconductor film and said gettering element in order to getter the metal in said semiconductor film

removing said portion after gettering the metal in said semiconductor film; and

forming a junction using an intrinsic semiconductor film.

89. (Amended) A method of manufacturing a device comprising the steps of:

providing a semiconductor film on an insulating surface;

forming a metal-containing material on said semiconductor film, said metal being a material which facilitates crystallization of said semiconductor film, but which when present in a final product of the device degrades operation of the device;

crystallizing said semiconductor film by heating in a way that causes said metal-containing material to diffuse into at least a part of the semiconductor film, said metal-containing material when so diffused functioning to facilitate said crystallization;

introducing a gettering element into a portion of the crystallized semiconductor film;

processing said semiconductor film after introducing said gettering element to remove at least one portion of said metal in said semiconductor film; and

removing said portion after gettering the metal in said semiconductor film.

Please add new claims 103-106 as follows.

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--103.(New) A method according to any one of claims
26, 34, 42, 51, 59, 67, 76, 82, or 86 wherein said gettering
layer is formed by a CVD method.

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104.(New) A method according to any one of claims 81,
83-85, or 87-89, wherein said gettering element comprises
phosphorus.

105.(New) A method according to any one of claims 81,
83-85, or 87-89, wherein said gettering ^{material} element is introduced by
a plasma doping method.

Sub
H1
106.(New) A method according to any one of claims 26,
34, 42, 51, 59, 67, 76, 82, or 86, wherein said gettering layer
is in contact with said semiconductor film.--